

1200V SiC Schottky Diode Module

Description

The SiC Schottky Diode Module G1 package devices are optimized to reduce losses and switching noise in high frequency power conditioning electrical systems.

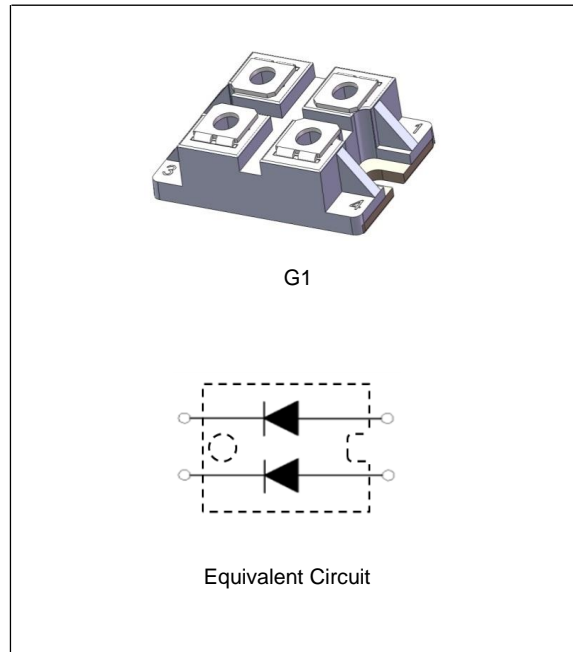
These SiC Schottky Diode Module series are ideally suited for Energy Storage ,High Power inverters, Power Quality Management and other applications where switching losses are significant portion of the total losses.

Features

- Revolutionary semiconductor material - Silicon Carbide
- No reverse recovery current
- Temperature independent switching behavior
- Excellent thermal performance
- High reliability
- Isolation Type Package

Applications

- Power Quality Management
- Energy Storage



Absolute Maximum Ratings (at $T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
V_{DC}	DC Blocking Voltage	1200	V
$I_{F(AVG)}$	Average Forward Current	$T_C \leq 145^\circ\text{C}$ 100	A
I_{FSM}	Non-Repetitive Forward Current , $t_p=8.3\text{ms}$, Half Sine Wave	600	A
P_D	Maximum Power Dissipation	500	W
T_J	Operating Junction Temperature Range	-55~+175	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55~+150	$^\circ\text{C}$
V_{iso}	Isolation Voltage	AC 1minute 2500	V
	Mounting screw Torque: M6	4	N.M
	Weight	300	g

Thermal Characteristics

Symbol	Parameter	Ratings	Unit
$R_{th(J-C)}$ (Diode)	Thermal Resistance, Junction to case for Diode	0.3	$^\circ\text{C/W}$

Electrical Characteristics of Diode @ $T_C=25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=100\text{A}$	-	1.6	1.9	V
		$I_F=100\text{A}, T_J=175^\circ\text{C}$	-	2.3	2.8	V
I_R	Reverse Current	$V_R=1200\text{V}$			300	μA
		$V_R=1200\text{V}, T_J=175^\circ\text{C}$			1000	μA
Q_C	Total Capacitive Charge	$V_R=800\text{V}, I_F=100\text{A}, di/dt=200\text{A}/\mu\text{s}$		290		nC
C	Total Capacitance	$V_R=800\text{V}, f=1\text{MHz}$		400		pF

Typical Performance Characteristics

Fig. 1. Forward Characteristics

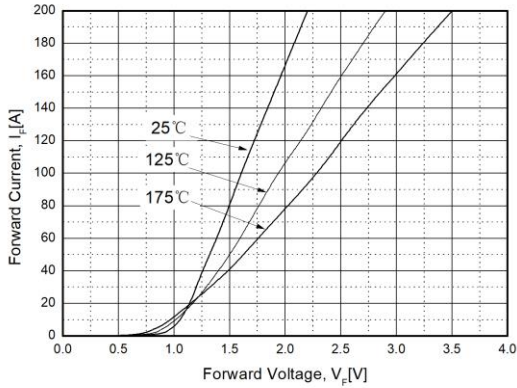


Fig. 2. Rate Current vs. T_C

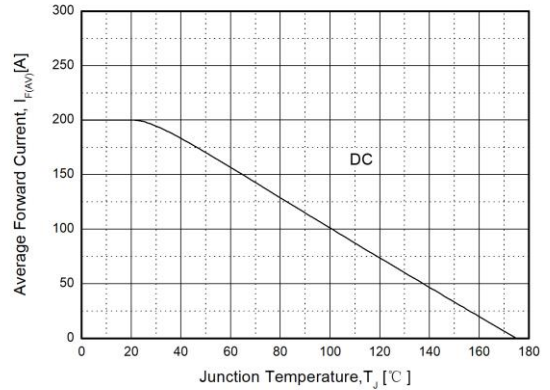


Fig. 3. Power Dissipation vs. T_J

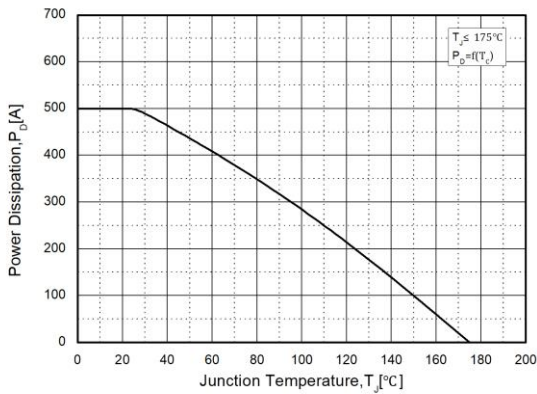


Fig. 4. Transient Thermal Impedance

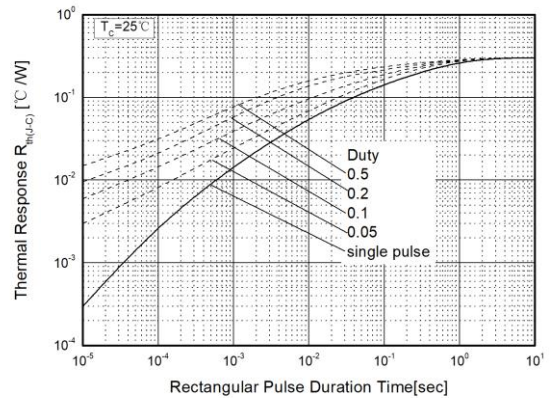


Fig. 5. Total Capacitance vs. Reverse Voltage

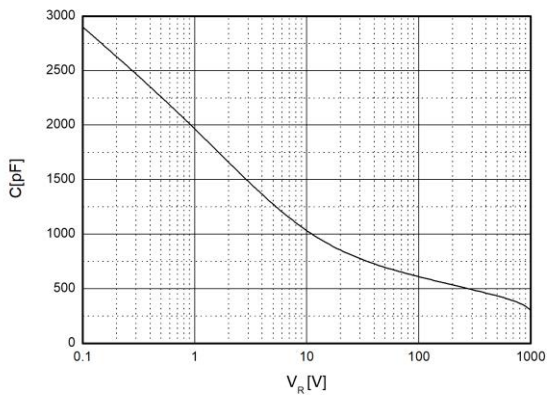
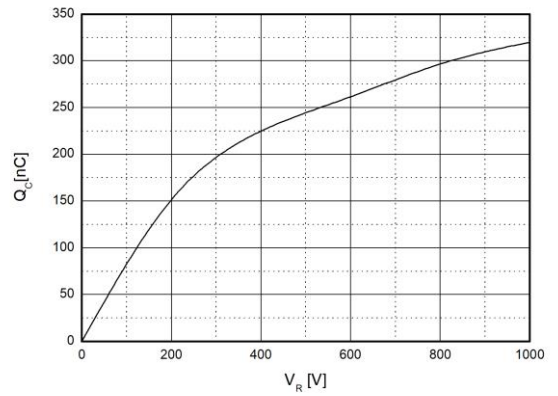
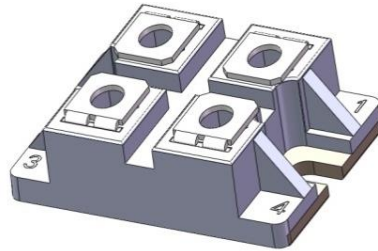


Fig. 6. Total Capacitive Charge vs. Reverse Voltage



Package Dimensions

G1



(Dimensions in Millimeters)

